Anti-Parallel
APT2X30D30JParallel
APT2X31D30J

**ADVANCED
POWER
TECHNOLOGY®**

APT2X31D30J 300V 30A
APT2X30D30J 300V 30A

DUAL DIE ISOTOP® PACKAGE

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS	PRODUCT FEATURES	PRODUCT BENEFITS
• Anti-Parallel Diode -Switchmode Power Supply -Inverters	• Ultrafast Recovery Times	• Low Losses
• Free Wheeling Diode -Motor Controllers -Converters	• Soft Recovery Characteristics	• Low Noise Switching
• Snubber Diode	• Popular SOT-227 Package	• Cooler Operation
• Uninterruptible Power Supply (UPS)	• Low Forward Voltage	• Higher Reliability Systems
• Induction Heating	• High Blocking Voltage	• Increased System Power Density
• High Speed Rectifiers	• Low Leakage Current	

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT2X31_30D30J	UNIT
V_R	Maximum D.C. Reverse Voltage	300	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 121^\circ\text{C}$, Duty Cycle = 0.5)	30	Amps
$I_{F(AV)}$	RMS Forward Current (Square wave, 50% duty)	53	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	320	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_L	Lead Temperature for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 30\text{A}$		1.2	1.4
		$I_F = 60\text{A}$		1.5	Volts
		$I_F = 30\text{A}, T_J = 125^\circ\text{C}$		1.0	
I_{RM}	Maximum Reverse Leakage Current	$V_R = V_R \text{ Rated}$		150	μA
		$V_R = V_R \text{ Rated}, T_J = 125^\circ\text{C}$		500	
C_T	Junction Capacitance, $V_R = 200\text{V}$		38		pF

DYNAMIC CHARACTERISTICS

APT2X31_30D30J

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time $I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ C$	$I_F = 30A, di_F/dt = -200A/\mu s$ $V_R = 200V, T_C = 25^\circ C$	-	20		ns
t_{rr}	Reverse Recovery Time		-	25		
Q_{rr}	Reverse Recovery Charge	$I_F = 30A, di_F/dt = -200A/\mu s$ $V_R = 200V, T_C = 25^\circ C$	-	28		nC
I_{RRM}	Maximum Reverse Recovery Current		-	2	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s$ $V_R = 200V, T_C = 125^\circ C$	-	55		ns
Q_{rr}	Reverse Recovery Charge		-	150		nC
I_{RRM}	Maximum Reverse Recovery Current		-	5	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30A, di_F/dt = -800A/\mu s$ $V_R = 200V, T_C = 125^\circ C$	-	33		ns
Q_{rr}	Reverse Recovery Charge		-	300		nC
I_{RRM}	Maximum Reverse Recovery Current		-	16		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.21	°C/W
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Min.)	2500			Volts
W_T	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

APT Reserves the right to change, without notice, the specifications and information contained herein.

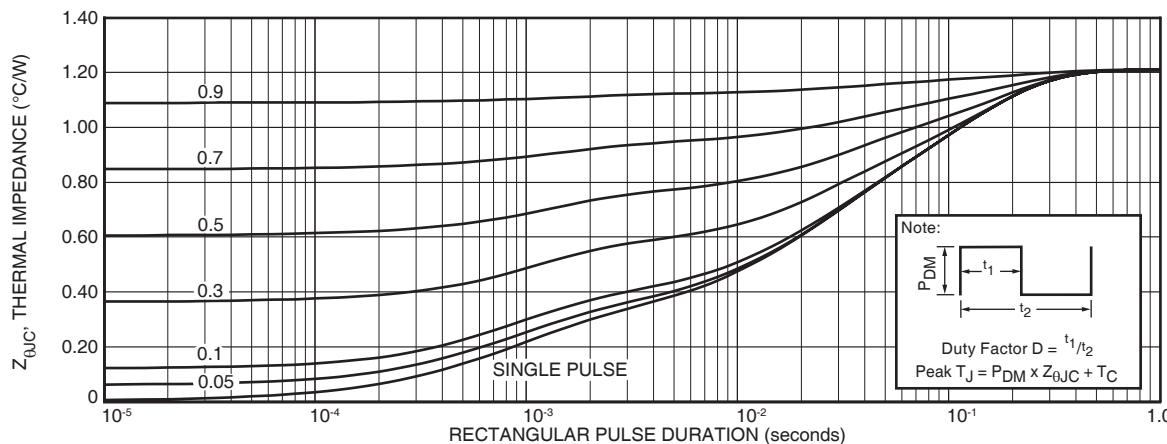


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

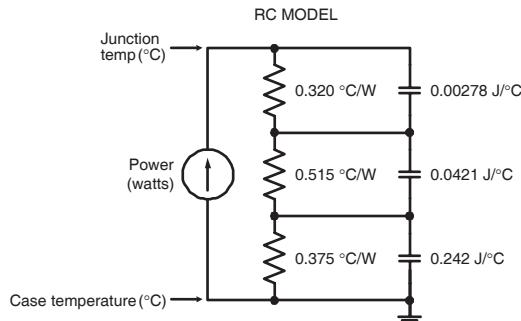


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

TYPICAL PERFORMANCE CURVES

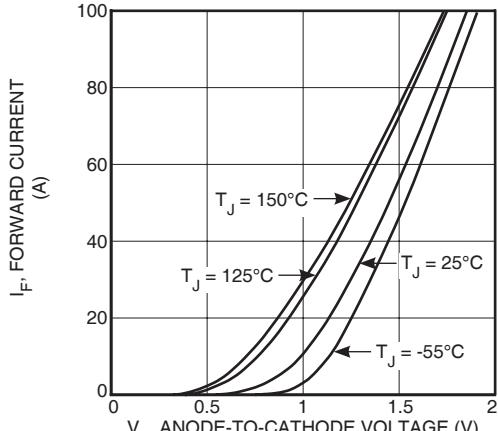


Figure 2. Forward Current vs. Forward Voltage

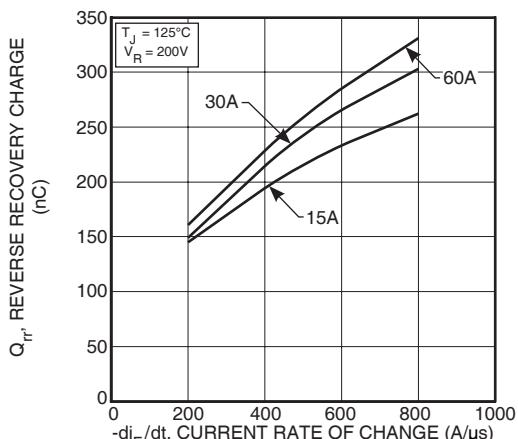


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

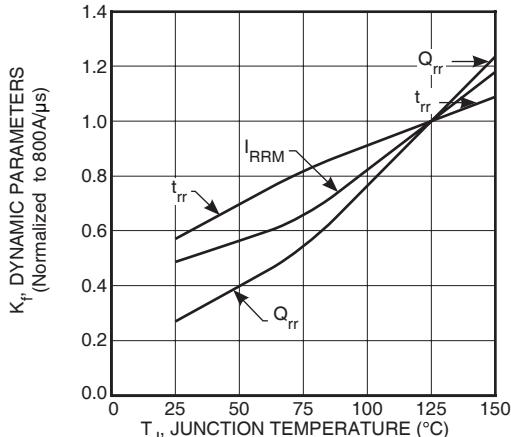


Figure 6. Dynamic Parameters vs. Junction Temperature

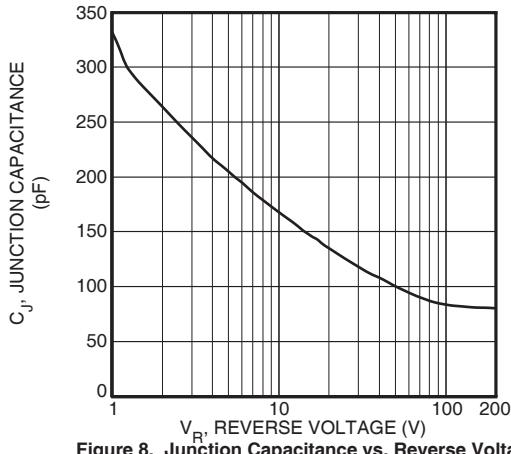


Figure 8. Junction Capacitance vs. Reverse Voltage

APT2X31_30D30J

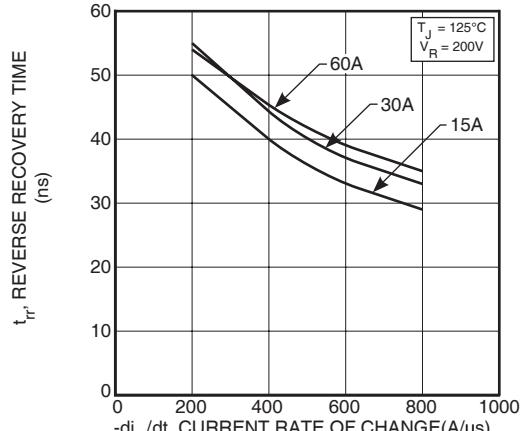


Figure 3. Reverse Recovery Time vs. Current Rate of Change

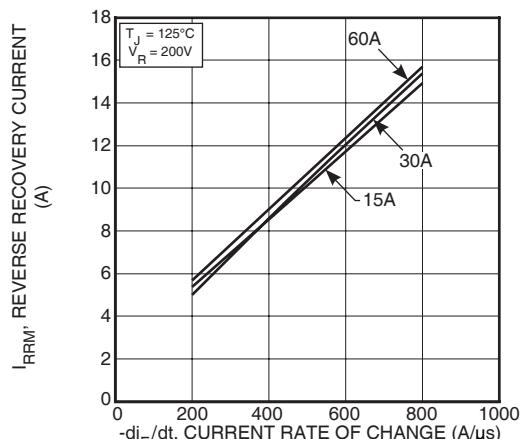


Figure 5. Reverse Recovery Current vs. Current Rate of Change

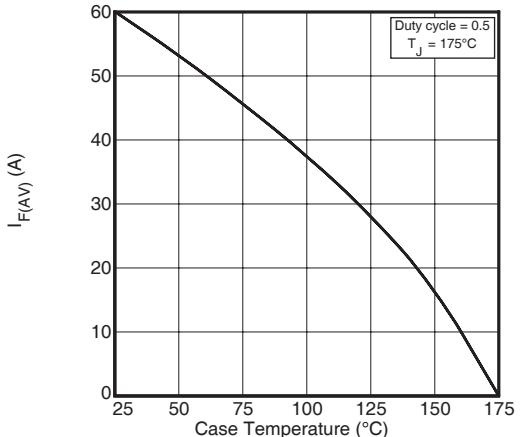


Figure 7. Maximum Average Forward Current vs. CaseTemperature

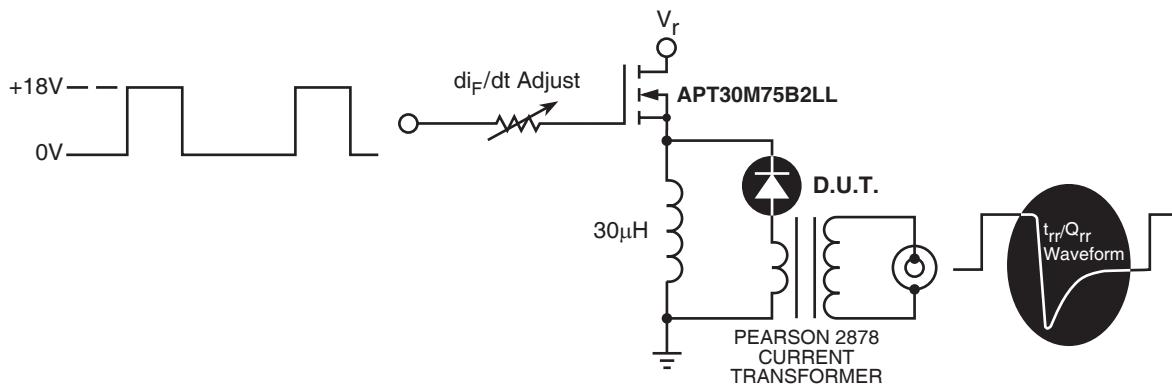


Figure 9. Diode Test Circuit

- ① I_F - Forward Conduction Current
- ② di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- ③ I_{RRM} - Maximum Reverse Recovery Current.
- ④ t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- ⑤ Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

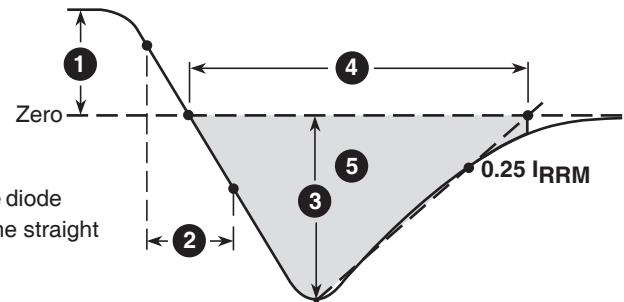
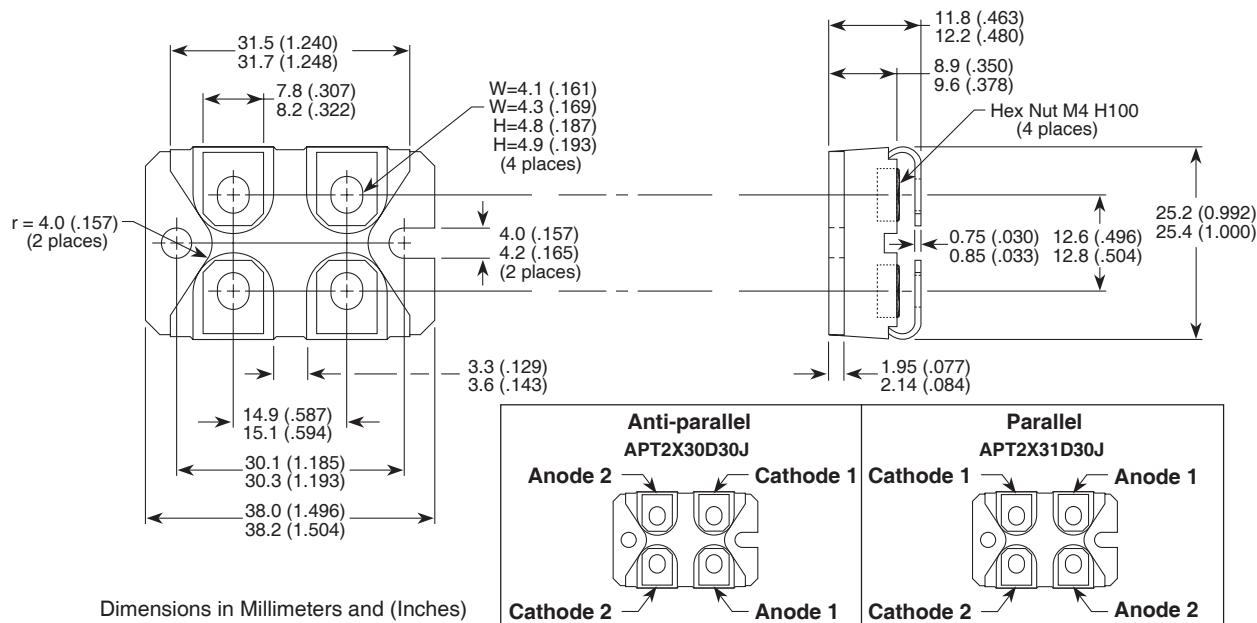


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

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